

Lasse Vines

List of Publications by Year in descending order

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184
papers

2,598
citations

279487

23
h-index

288905

40
g-index

190
all docs

190
docs citations

190
times ranked

2659
citing authors

#	ARTICLE	IF	CITATIONS
1	Iron and intrinsic deep level states in Ga ₂ O ₃ . Applied Physics Letters, 2018, 112, .	1.5	196
2	Self-compensation in semiconductors: The Zn vacancy in Ga-doped ZnO. Physical Review B, 2011, 84, .	1.1	169
3	Impact of proton irradiation on conductivity and deep level defects in $\hat{\Gamma}^2$ -Ga ₂ O ₃ . APL Materials, 2019, 7, .	2.2	143
4	Self-trapped hole and impurity-related broad luminescence in $\hat{\Gamma}^2$ -Ga ₂ O ₃ . Journal of Applied Physics, 2020, 127, .	1.1	87
5	Ultra-doped n-type germanium thin films for sensing in the mid-infrared. Scientific Reports, 2016, 6, 27643.	1.6	64
6	Electrical charge state identification and control for the silicon vacancy in 4H-SiC. Npj Quantum Information, 2019, 5, .	2.8	54
7	Zinc-Vacancy "Donor Complex: A Crucial Compensating Acceptor in ZnO. Physical Review Applied, 2014, 2, .	1.5	51
8	Bifacial Kesterite Solar Cells on FTO Substrates. ACS Sustainable Chemistry and Engineering, 2017, 5, 11516-11524.	3.2	45
9	Lithium and electrical properties of ZnO. Journal of Applied Physics, 2010, 107, .	1.1	44
10	Evolution of deep electronic states in ZnO during heat treatment in oxygen- and zinc-rich ambients. Applied Physics Letters, 2012, 100, 112108.	1.5	43
11	Aluminum Migration and Intrinsic Defect Interaction in Single-Crystal Zinc Oxide. Physical Review Applied, 2015, 3, .	1.5	38
12	Ti- and Fe-related charge transition levels in $\hat{\Gamma}^2$ -Ga ₂ O ₃ . Applied Physics Letters, 2020, 116, .	1.5	37
13	Conversion pathways of primary defects by annealing in proton-irradiated n-type 4H-SiC. Physical Review B, 2020, 102, .	1.1	36
14	Persistent Double-Layer Formation in Kesterite Solar Cells: A Critical Review. ACS Applied Materials & Interfaces, 2020, 12, 39405-39424.	4.0	35
15	Monolithic thin-film chalcogenide "silicon tandem solar cells enabled by a diffusion barrier. Solar Energy Materials and Solar Cells, 2020, 207, 110334.	3.0	34
16	The work function of n-ZnO deduced from heterojunctions with Si prepared by ALD. Journal Physics D: Applied Physics, 2012, 45, 315101.	1.3	31
17	Transition-Metal Oxides for Kesterite Solar Cells Developed on Transparent Substrates. ACS Applied Materials & Interfaces, 2020, 12, 33656-33669.	4.0	29
18	Defect evolution and impurity migration in Na-implanted ZnO. Physical Review B, 2011, 84, .	1.1	28

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19	Intrinsic Point-Defect Balance in Self-Ion-Implanted ZnO. <i>Physical Review Letters</i> , 2013, 110, 015501.	2.9	28
20	Multistability of isolated and hydrogenated Ga ²⁺ O divacancies in Ga_2O_3 . <i>Physical Review Materials</i> , 2021, 5, .	0.9	28
21	On the permittivity of titanium dioxide. <i>Scientific Reports</i> , 2021, 11, 12443.	1.6	28
22	Bulk Ga_2O_3 with (010) and (201) Surface Orientation: Schottky Contacts and Point Defects. <i>Materials Science Forum</i> , 0, 897, 755-758.	0.3	27
23	Manipulating Single-Photon Emission from Point Defects in Diamond and Silicon Carbide. <i>Advanced Quantum Technologies</i> , 2021, 4, 2100003.	1.8	25
24	Interplay of vacancies, hydrogen, and electrical compensation in irradiated and annealed In_2O_3 -type In_2O_3 . <i>Journal of Applied Physics</i> , 2021, 129, .	1.1	24
25	Primary intrinsic defects and their charge transition levels in Ga_2O_3 . <i>Physical Review Materials</i> , 2020, 4, .	0.9	21
26	Formation and origin of the dominating electron trap in irradiated p -type silicon. <i>Physical Review B</i> , 2008, 78, .	1.1	20
27	The E3 center in zinc oxide: Evidence for involvement of hydrogen. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	20
28	On the recombination centers of iron-gallium pairs in Ga-doped silicon. <i>Journal of Applied Physics</i> , 2017, 122, .	1.1	20
29	Strong Interplay between Sodium and Oxygen in Kesterite Absorbers: Complex Formation, Incorporation, and Tailoring Depth Distributions. <i>Advanced Energy Materials</i> , 2019, 9, 1900740.	10.2	20
30	Anisotropic and plane-selective migration of the carbon vacancy in SiC: Theory and experiment. <i>Physical Review B</i> , 2019, 100, .	1.1	20
31	Highly Correlated Hydride Ion Tracer Diffusion in SrTiO_3H_x Oxyhydrides. <i>Journal of the American Chemical Society</i> , 2019, 141, 4653-4659.	6.6	20
32	Defects in virgin hydrothermally grown n-type ZnO studied by temperature dependent Hall effect measurements. <i>Journal of Applied Physics</i> , 2009, 106, .	1.1	19
33	Defect formation and thermal stability of H in high dose H implanted ZnO. <i>Journal of Applied Physics</i> , 2013, 114, 083111.	1.1	19
34	Direct observation of conduction band plasmons and the related Burstein-Moss shift in highly doped semiconductors: A STEM-EELS study of Ga-doped ZnO. <i>Physical Review B</i> , 2018, 98, .	1.1	19
35	Nitride-Based Interfacial Layers for Monolithic Tandem Integration of New Solar Energy Materials on Si: The Case of CZTS. <i>ACS Applied Energy Materials</i> , 2020, 3, 4600-4609.	2.5	19
36	The use of nanocavities for the fabrication of ultrathin buried oxide layers. <i>Applied Physics Letters</i> , 2009, 94, 011903.	1.5	18

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37	Impact of growth rate on impurities segregation at grain boundaries in silicon during Bridgman growth. <i>Journal of Crystal Growth</i> , 2013, 372, 180-188.	0.7	18
38	Influence of Oxygen Pressure on Growth of Si-Doped $\text{Al}_{1-x}\text{Ga}_x$ Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 707 Deposition. <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, Q3217-Q3220.	0.9	18
39	Formation and control of the $\text{E}_2^{\text{A}^-}$ center in implanted Ga_2O_3 by reverse-bias and zero-bias annealing. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 464001.	1.3	18
40	Effect of spatial defect distribution on the electrical behavior of prominent vacancy point defects in swift-ion implanted Si. <i>Physical Review B</i> , 2009, 79, .	1.1	17
41	Interaction between Na and Li in ZnO. <i>Applied Physics Letters</i> , 2009, 95, 242111.	1.5	17
42	Radiation-induced defect accumulation and annealing in Si-implanted gallium oxide. <i>Journal of Applied Physics</i> , 2022, 131, .	1.1	17
43	Anisotropic and trap-limited diffusion of hydrogen/deuterium in monoclinic gallium oxide single crystals. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	16
44	Acceptor-like deep level defects in ion-implanted ZnO. <i>Applied Physics Letters</i> , 2012, 100, 212106.	1.5	15
45	Impurity Sublattice Localization in ZnO Revealed by Li Marker Diffusion. <i>Physical Review Letters</i> , 2013, 110, 175503.	2.9	15
46	Electrical conductivity of In_2O_3 and Ga_2O_3 after low temperature ion irradiation; implications for intrinsic defect formation and charge neutrality level. <i>Journal of Physics Condensed Matter</i> , 2018, 30, 025502.	0.7	15
47	Electronic properties of vacancy related defects in ZnO induced by mechanical polishing. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	14
48	Hydrogen engineering via plasma immersion ion implantation and flash lamp annealing in silicon-based solar cell substrates. <i>Journal of Applied Physics</i> , 2014, 115, 064505.	1.1	14
49	Evolution kinetics of elementary point defects in ZnO implanted with low fluences of helium at cryogenic temperature. <i>Physical Review B</i> , 2016, 94, .	1.1	14
50	Practical limitations to selenium annealing of compound co-sputtered $\text{Cu}_2\text{ZnSnS}_4$ as a route to achieving sulfur-selenium graded solar cell absorbers. <i>Thin Solid Films</i> , 2017, 623, 110-115.	0.8	14
51	Formation of Zn- and O- vacancy clusters in ZnO through deuterium annealing. <i>Materials Science in Semiconductor Processing</i> , 2017, 69, 23-27.	1.9	14
52	Evidence of defect band mechanism responsible for band gap evolution in ZnO alloys. <i>Physical Review B</i> , 2019, 100, .	1.1	14
53	Influence of hydrogen implantation on emission from the silicon vacancy in 4H-SiC. <i>Journal of Applied Physics</i> , 2020, 127, .	1.1	14
54	Visualization of MeV ion impacts in Si using scanning capacitance microscopy. <i>Physical Review B</i> , 2006, 73, .	1.1	13

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55	Effect of high temperature treatments on defect centers and impurities in hydrothermally grown ZnO. <i>Physica B: Condensed Matter</i> , 2009, 404, 4386-4388.	1.3	13
56	Defects in p-type Cz-silicon irradiated at elevated temperatures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 2009-2012.	0.8	13
57	Transformation of divacancies to divacancy-oxygen pairs in p-type Czochralski-silicon; mechanism of divacancy diffusion. <i>Journal of Applied Physics</i> , 2014, 115, 034514.	1.1	13
58	Band-gap narrowing in Mn-doped GaAs probed by room-temperature photoluminescence. <i>Physical Review B</i> , 2015, 92, .	1.1	13
59	Formation and annihilation of E4 centers in ZnO: Influence of hydrogen. <i>Journal of Applied Physics</i> , 2016, 119, .	1.1	13
60	Gallium diffusion in zinc oxide via the paired dopant-vacancy mechanism. <i>Journal of Applied Physics</i> , 2018, 123, .	1.1	13
61	Generation and metastability of deep level states in \hat{I}^2 -Ga ₂ O ₃ exposed to reverse bias at elevated temperatures. <i>Journal of Applied Physics</i> , 2019, 125, 185706.	1.1	13
62	Negative-U and polaronic behavior of the Zn-O divacancy in ZnO. <i>Physical Review B</i> , 2019, 99, .	1.1	13
63	Lateral straggling of implanted aluminum in 4H-SiC. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	13
64	High electron mobility single-crystalline ZnSn ₂ on ZnO (0001) substrates. <i>CrystEngComm</i> , 2020, 22, 6268-6274.	1.3	13
65	Electronic properties of n-ZnO(Al)/p-Si heterojunction prepared by dc magnetron sputtering. <i>Thin Solid Films</i> , 2011, 519, 5763-5766.	0.8	12
66	Composition and structure of Pd nanoclusters in SiO _x thin film. <i>Journal of Applied Physics</i> , 2011, 109, 084329.	1.1	12
67	Iron related donor-like defect in zinc oxide. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	12
68	Phosphorus in-diffusion from a surface source by millisecond flash lamp annealing for shallow emitter solar cells. <i>Applied Physics Letters</i> , 2013, 102, 132108.	1.5	12
69	Silver migration and trapping in ion implanted ZnO single crystals. <i>Journal of Applied Physics</i> , 2016, 119, .	1.1	12
70	Role of Nitrogen in Defect Evolution in Zinc Oxide: STEM-EELS Nanoscale Investigations. <i>Journal of Physical Chemistry Letters</i> , 2019, 10, 4725-4730.	2.1	12
71	Bulk In ₂ O ₃ crystals grown by chemical vapour transport: a combination of XPS and DFT studies. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 18753-18758.	1.1	12
72	Recent Advances in the Doping of 4H-SiC by Channeled Ion Implantation. <i>Materials Science Forum</i> , 0, 963, 375-381.	0.3	12

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73	Preferential Grain Etching of AlMgSi(Zn) Model Alloys. Journal of the Electrochemical Society, 2010, 157, C424.	1.3	11
74	Li and OH-Li Complexes in Hydrothermally Grown Single-Crystalline ZnO. Journal of Electronic Materials, 2011, 40, 429-432.	1.0	11
75	Ion implantation induced defects in ZnO. Physica B: Condensed Matter, 2012, 407, 1481-1484.	1.3	11
76	Strain Modulation of Si Vacancy Emission from SiC Micro- and Nanoparticles. Nano Letters, 2020, 20, 8689-8695.	4.5	11
77	Influence of heat treatments in H ₂ and Ar on the $E_{1/2}$ center in In^{2+} -Ga ₂ O ₃ . Journal of Applied Physics, 2022, 131, .	1.1	11
78	Formation of donor and acceptor states of the divacancy-oxygen centre in p-type Cz-silicon. Journal of Physics Condensed Matter, 2012, 24, 435801.	0.7	10
79	The effect of millisecond flash lamp annealing on electrical and structural properties of ZnO:Al/Si structures. Journal of Applied Physics, 2016, 119, 185305.	1.1	10
80	The temperature-dependency of the optical band gap of ZnO measured by electron energy-loss spectroscopy in a scanning transmission electron microscope. Journal of Applied Physics, 2018, 123, .	1.1	10
81	Intentional and unintentional channeling during implantation of ^{51}V ions into 4H-SiC. Semiconductor Science and Technology, 2019, 34, 115006.	1.0	10
82	Role of intrinsic and extrinsic defects in H implanted hydrothermally grown ZnO. Journal of Applied Physics, 2019, 126, 125707.	1.1	10
83	Combining steady-state photo-capacitance spectra with first-principles calculations: the case of Fe and Ti in In^{2+} -Ga ₂ O ₃ . New Journal of Physics, 2020, 22, 063033.	1.2	10
84	ZnSnN ₂ in Real Space and k-Space: Lattice Constants, Dislocation Density, and Optical Band Gap. Advanced Optical Materials, 2021, 9, 2100015.	3.6	10
85	Correlation between nitrogen and carbon incorporation into MOVPE ZnO at various oxidizing conditions. Microelectronics Journal, 2009, 40, 232-235.	1.1	9
86	Electronic states at the interface between indium tin oxide and silicon. Journal of Applied Physics, 2011, 110, .	1.1	9
87	Influence of pulling rate on multicrystalline silicon ingots' properties. Journal of Crystal Growth, 2014, 386, 199-203.	0.7	9
88	Channeled Implantations of p-Type Dopants into 4H-SiC at Different Temperatures. Materials Science Forum, 0, 963, 382-385.	0.3	9
89	Boron Electrical Activation in Crystalline Si after Millisecond Nonmelting Laser Irradiation. Journal of the Electrochemical Society, 2008, 155, H603.	1.3	8
90	Effects of high temperature annealing on defects and luminescence properties in H implanted ZnO. Journal Physics D: Applied Physics, 2014, 47, 342001.	1.3	8

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91	Blue luminescence from donor-complexed LiZn and NaNaZn acceptors in ZnO. <i>Physical Review B</i> , 2019, 100, .	1.1	8
92	Defect annealing kinetics in ZnO implanted with Zn substituting elements: Zn interstitials and Li redistribution. <i>Journal of Applied Physics</i> , 2019, 125, .	1.1	8
93	Deep level study of chlorine-based dry etched $\text{Li}^2\text{Ga}2\text{O}_3$. <i>Journal of Applied Physics</i> , 2021, 130, .	1.1	8
94	Influence from the electronic shell structure on the range distribution during channeling of 40keV ions in 4H-SiC. <i>Journal of Applied Physics</i> , 2021, 130, .	1.1	8
95	Electrical Characterization of Hydrothermally Grown ZnO Annealed in Different Atmospheres. <i>International Journal of Applied Ceramic Technology</i> , 2011, 8, 1017-1022.	1.1	7
96	Interaction between hydrogen and the Fe-B pair in boron-doped p-type silicon. <i>Applied Physics Letters</i> , 2011, 99, 052106.	1.5	7
97	Electronic Properties of ZnO/Si Heterojunction Prepared by ALD.. <i>Solid State Phenomena</i> , 0, 178-179, 130-135.	0.3	7
98	Al and Si doping of sputtered ZnO thin films. <i>IOP Conference Series: Materials Science and Engineering</i> , 2012, 34, 012007.	0.3	7
99	Bulk Growth and Impurities. <i>Semiconductors and Semimetals</i> , 2013, 88, 67-104.	0.4	7
100	Hydrogen induced optically-active defects in silicon photonic nanocavities. <i>Optics Express</i> , 2014, 22, 8843.	1.7	7
101	Coincident site lattice bi-crystals growth Impurity segregation towards grain boundaries. <i>Journal of Crystal Growth</i> , 2015, 416, 8-11.	0.7	7
102	Enhancement of carrier mobility in thin Ge layer by Sn co-doping. <i>Semiconductor Science and Technology</i> , 2016, 31, 105012.	1.0	7
103	Influence of Fermi level position on vacancy-assisted diffusion of aluminum in zinc oxide. <i>Physical Review B</i> , 2018, 98, .	1.1	7
104	Surface Erosion of Ion-Implanted 4H-SiC during Annealing with Carbon Cap. <i>Materials Science Forum</i> , 0, 924, 373-376.	0.3	7
105	Bandgap bowing in crystalline ZnO (GaN) thin films; influence of composition and structural properties. <i>Semiconductor Science and Technology</i> , 2019, 34, M1500	1.0	7
106	Interaction with Negative-U and High-Spin-State Defects: Differentiating Between UC and C and Si	1.5	7
107	Experimental exploration of the amphoteric defect model by cryogenic ion irradiation of a range of wide band gap oxide materials. <i>Journal of Physics Condensed Matter</i> , 2020, 32, 415704.	0.7	7
108	Formation of carbon interstitial-related defect levels by thermal injection of carbon into n-type H-SiC. <i>Journal of Applied Physics</i> , 2022, 131, .	1.1	7

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109	Defect and dopant kinetics in laser anneals of Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 154-155, 35-38.	1.7	6
110	Preferential Grain Etching of AlMgSi(Zn) Model Alloys. ECS Transactions, 2010, 25, 71-79.	0.3	6
111	Equilibrium shape of nano-cavities in H implanted ZnO. Applied Physics Letters, 2015, 106, .	1.5	6
112	Limitation of Na-H codoping in achieving device-quality p-type ZnO. Materials Science in Semiconductor Processing, 2017, 69, 28-31.	1.9	6
113	Complementary study of the photoluminescence and electrical properties of ZnO films grown on 4H-SiC substrates. Journal of Luminescence, 2017, 181, 374-381.	1.5	6
114	Influence of annealing atmosphere on formation of electrically-active defects in rutile TiO ₂ . Journal of Applied Physics, 2018, 123, 161572.	1.1	6
115	Selenium Inclusion in Cu ₂ ZnSn(S,Se) ₄ Solar Cell Absorber Precursors for Optimized Grain Growth. IEEE Journal of Photovoltaics, 2018, 8, 1132-1141.	1.5	6
116	Optical signatures of single ion tracks in ZnO. Nanoscale Advances, 2020, 2, 724-733.	2.2	6
117	Spatially Resolved Diffusion of Aluminum in 4H-SiC During Postimplantation Annealing. IEEE Transactions on Electron Devices, 2020, 67, 4360-4365.	1.6	6
118	Donors and polaronic absorption in rutile TiO ₂ single crystals. Journal of Applied Physics, 2020, 128, 145701.	1.1	6
119	Formation of N ₂ bubbles along grain boundaries in (ZnO) _{1-x} (GaN) _x : nanoscale STEM-EELS studies. Physical Chemistry Chemical Physics, 2020, 22, 3779-3783.	1.3	6
120	Activation energy of silicon diffusion in gallium oxide: Roles of the mediating defects charge states and phase modification. Applied Physics Letters, 2021, 119, .	1.5	6
121	Hydrothermally Grown Single-Crystalline Zinc Oxide; Characterization and Modification. Materials Research Society Symposia Proceedings, 2007, 1035, 1.	0.1	5
122	Hydrogen Decoration of Vacancy Related Complexes in Hydrogen Implanted Silicon. Solid State Phenomena, 0, 178-179, 192-197.	0.3	5
123	Single-crystal TiO ₂ nanowires by seed assisted thermal oxidation of Ti foil: synthesis and photocatalytic properties. RSC Advances, 2016, 6, 55490-55498.	1.7	5
124	Comparison of the structural properties of Zn-face and O-face single crystal homoepitaxial ZnO epilayers grown by RF-magnetron sputtering. Journal of Applied Physics, 2017, 121, .	1.1	5
125	Photoinduced small polarons bound to hydrogen defects in rutile TiO_2 . Physical Review B, 2017, 96, .	1.1	5
126	Low temperature incorporation of selenium in Cu ₂ ZnSnS ₄ : Diffusion and nucleation. Thin Solid Films, 2018, 665, 159-163.	0.8	5

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127	Diffusion of the Carbon Vacancy in a-Cut and c-Cut n-Type 4H-SiC. Materials Science Forum, 0, 924, 200-203.	0.3	5
128	Nanoscale n++-p junction formation in GeOI probed by tip-enhanced Raman spectroscopy and conductive atomic force microscopy. Journal of Applied Physics, 2019, 125, 245703.	1.1	5
129	Effects of Substrate and Post-Deposition Annealing on Structural and Optical Properties of (ZnO) _{1-x} (GaN) _x Films. Physica Status Solidi (B): Basic Research, 2019, 256, 1800529.	0.7	5
130	Fabrication and characterization of Schottky barrier diodes on rutile TiO ₂ . Materials Research Express, 2020, 7, 065903.	0.8	5
131	First-principles calculations of Stark shifts of electronic transitions for defects in semiconductors: the Si vacancy in 4H-SiC. Journal of Physics Condensed Matter, 2020, 33, 075502.	0.7	5
132	Secondary ion mass spectrometry as a tool to study selenium gradient in Cu ₂ ZnSn(S,Se) ₄ . Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, 1600187.	0.8	5
133	Study of defect engineering in the initial stage of SIMOX processing. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 161-164.	0.6	4
134	Impurity migration in bulk and thin-film ZnO. Physica Scripta, 2012, T148, 014005.	1.2	4
135	Divacancy-iron complexes in silicon. Journal of Applied Physics, 2013, 113, 044503.	1.1	4
136	Subsurface damage in polishing-annealing processed ZnO substrates. Materials Science in Semiconductor Processing, 2017, 69, 19-22.	1.9	4
137	Formation and evolution of E3 centers in hydrothermally grown zinc oxide. Materials Science in Semiconductor Processing, 2017, 69, 13-18.	1.9	4
138	ZnCr ₂ O ₄ Inclusions in ZnO Matrix Investigated by Probe-Corrected STEM-EELS. Materials, 2019, 12, 888.	1.3	4
139	Diffusion of indium in single crystal zinc oxide: a comparison between group III donors. Semiconductor Science and Technology, 2019, 34, 025011.	1.0	4
140	Intentional and Unintentional Channeling during Implantation of p-Dopants in 4H-SiC. Materials Science Forum, 0, 1004, 689-697.	0.3	4
141	Dynamic Impurity Redistributions in Kesterite Absorbers. Physica Status Solidi (B): Basic Research, 2020, 257, 2000062.	0.7	4
142	Fermi level controlled point defect balance in ion irradiated indium oxide. Journal of Applied Physics, 2021, 130, 085703.	1.1	4
143	Hydrogen-related defects in boron doped p-type silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 705-708.	0.8	3
144	Long range lateral migration of intrinsic point defects in n-type 4H-SiC. Journal of Applied Physics, 2012, 111, 103719.	1.1	3

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145	Deep level transient spectroscopy on proton-irradiated Fe-contaminated p-type silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1992-1995.	0.8	3
146	Formation kinetics of trivacancy-oxygen pairs in silicon. Journal of Applied Physics, 2014, 116, 124510.	1.1	3
147	Zn precipitation and Li depletion in Zn implanted ZnO. Applied Physics Letters, 2016, 109, 022102.	1.5	3
148	Structural and optical properties of individual Zn ₂ GeO ₄ particles embedded in ZnO. Nanotechnology, 2019, 30, 225702.	1.3	3
149	Formation and Characterization of Shallow Junctions in GaAs Made by Ion Implantation and ms-Range Flash Lamp Annealing. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800618.	0.8	3
150	Dominant hydrogen complex in natural anatase TiO ₂ . Journal of Applied Physics, 2021, 130, 145701.	1.1	3
151	Gettering in PolySi/SiO _x Passivating Contacts Enables Si-Based Tandem Solar Cells with High Thermal and Contamination Resilience. ACS Applied Materials & Interfaces, 2022, 14, 14342-14358.	4.0	3
152	A Laterally Resolved DLTS Study of Intrinsic Defect Diffusion in 4H-SiC after Low Energy Focused Proton Beam Irradiation. Materials Science Forum, 0, 645-648, 431-434.	0.3	2
153	Effect of the crystallinity of MOCVD-grown ZnO:N on the diffusion of impurities. Journal of Crystal Growth, 2011, 324, 243-247.	0.7	2
154	Anomalous Diffusion of Intrinsic Defects in K ⁺ Implanted ZnO using Li as Tracer. Materials Research Society Symposia Proceedings, 2012, 1394, 75.	0.1	2
155	Formation of Single and Double Donor States of Trivacancy-Oxygen Complexes in P-Type Silicon. Solid State Phenomena, 0, 205-206, 213-217.	0.3	2
156	Dopant incorporation in Al _{0.9} Ga _{0.1} As _{0.06} Sb _{0.94} grown by molecular beam epitaxy. Journal of Crystal Growth, 2017, 463, 116-122.	0.7	2
157	Influence of a thin amorphous surface layer on de-channeling during aluminum implantation at different temperatures into 4H-SiC. Applied Physics A: Materials Science and Processing, 2019, 125, 1.	1.1	2
158	Influence of Carbon Cap on Self-Diffusion in Silicon Carbide. Crystals, 2020, 10, 752.	1.0	2
159	Phosphorus implantation into 4H-SiC at room and elevated temperature. Semiconductor Science and Technology, 2021, 36, 065002.	1.0	2
160	Resolving Jahn-Teller induced vibronic fine structure of silicon vacancy quantum emission in silicon carbide. Physical Review B, 2021, 104, .	1.1	2
161	Formation and functionalization of Ge-nanoparticles in ZnO. Nanotechnology, 2021, 32, 505707.	1.3	2
162	Highly Active Junctions Formed in Crystalline Silicon by Infrared Laser Annealing. , 2007, , .		1

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163	Scanning spreading resistance microscopy of defect engineered low dose SIMOX samples. Microelectronic Engineering, 2007, 84, 547-550.	1.1	1
164	Formation and annealing behavior of prominent point defects in MeV ion implanted n-type epitaxial Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 159-160, 177-181.	1.7	1
165	Identification of Grain Boundary Segregation Mechanisms during Silicon Bi-Crystal Solidification. Materials Science Forum, 2014, 790-791, 329-334.	0.3	1
166	Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. ECS Journal of Solid State Science and Technology, 2017, 6, P741-P745.	0.9	1
167	(Invited) Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. ECS Transactions, 2017, 80, 107-115.	0.3	1
168	The interaction between lithium acceptors and gallium donors in zinc oxide. Journal of Applied Physics, 2018, 124, 245702.	1.1	1
169	Increased dephasing length in heavily doped GaAs. New Journal of Physics, 2021, 23, 083034.	1.2	1
170	Electrically-active defects in reduced and hydrogenated rutile TiO ₂ . Semiconductor Science and Technology, 2021, 36, 014006.	1.0	1
171	Scanning probe microscopy of single Au ion implants in Si. Materials Science and Engineering C, 2006, 26, 782-787.	3.8	0
172	Thermal and non-thermal kinetics of defects and dopant in Si. , 2008, , .		0
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